

Refine Search*10/8/9592***Search Results -**

Terms	Documents
L3 and bath and (energy or voltage)	7

Database: US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Search:**Refine Search****Recall Text****Clear****Interrupt**

Search History

DATE: Thursday, March 03, 2005 [Printable Copy](#) [Create Case](#)**Set Name Query**
side by side**Hit Count Set Name**
result set*DB=USPT; PLUR=YES; OP=ADJ*

<u>L4</u>	L3 and bath and (energy or voltage)	7	<u>L4</u>
<u>L3</u>	L1 and hydrophobic	69	<u>L3</u>
<u>L2</u>	L1 near5 hydrophobic	0	<u>L2</u>
<u>L1</u>	copper near4 (encased or embedded)	1969	<u>L1</u>

END OF SEARCH HISTORY

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Search Results - Record(s) 1 through 7 of 7 returned.

1. Document ID: US 6709555 B1

L4: Entry 1 of 7

File: USPT

Mar 23, 2004

US-PAT-NO: 6709555

DOCUMENT-IDENTIFIER: US 6709555 B1

** See image for Certificate of Correction **

TITLE: Plating method, interconnection forming method, and apparatus for carrying out those methods

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMDC	Drawn
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2. Document ID: US 6261433 B1

L4: Entry 2 of 7

File: USPT

Jul 17, 2001

US-PAT-NO: 6261433

DOCUMENT-IDENTIFIER: US 6261433 B1

** See image for Certificate of Correction **

TITLE: Electro-chemical deposition system and method of electroplating on substrates

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMDC	Drawn
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3. Document ID: US 5167857 A

L4: Entry 3 of 7

File: USPT

Dec 1, 1992

US-PAT-NO: 5167857

DOCUMENT-IDENTIFIER: US 5167857 A

** See image for Certificate of Correction **

TITLE: Lactic acid derivative, liquid crystal composition containing same and liquid crystal device

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMDC	Drawn
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4. Document ID: US 5143643 A

L4: Entry 4 of 7

File: USPT

Sep 1, 1992

US-PAT-NO: 5143643

DOCUMENT-IDENTIFIER: US 5143643 A

**** See image for Certificate of Correction ****

TITLE: Optically active mesomorphic compound

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KINIC](#) | [Drawn](#)

5. Document ID: US 5114613 A

L4: Entry 5 of 7

File: USPT

May 19, 1992

US-PAT-NO: 5114613

DOCUMENT-IDENTIFIER: US 5114613 A

TITLE: Lactic acid derivative and liquid crystal composition containing same

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KINIC](#) | [Drawn](#)

6. Document ID: US 4882085 A

L4: Entry 6 of 7

File: USPT

Nov 21, 1989

US-PAT-NO: 4882085

DOCUMENT-IDENTIFIER: US 4882085 A

**** See image for Certificate of Correction ****

TITLE: Lactic acid derivative and liquid crystal composition containing same

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KINIC](#) | [Drawn](#)

7. Document ID: US 4775223 A

L4: Entry 7 of 7

File: USPT

Oct 4, 1988

US-PAT-NO: 4775223

DOCUMENT-IDENTIFIER: US 4775223 A

**** See image for Certificate of Correction ****

TITLE: Lactic acid derivative, liquid crystal composition containing same and liquid crystal device

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KINIC](#) | [Drawn](#)

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Terms	Documents
L3 and bath and (energy or voltage)	7

Display Format:

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Refine Search

10/8/4592

Search Results -

Terms	Documents
L12 and copper	2

Database:

- US Pre-Grant Publication Full-Text Database
- US Patents Full-Text Database**
- US OCR Full-Text Database
- EPO Abstracts Database
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- Derwent World Patents Index
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Search: L13

Search History

DATE: Thursday, March 03, 2005 [Printable Copy](#) [Create Case](#)

Set Name Query
side by side

Hit Count Set Name
result set

DB=USPT; PLUR=YES; OP=ADJ

<u>L13</u>	L12 and copper	2	<u>L13</u>
<u>L12</u>	L10 and interlayer	8	<u>L12</u>
<u>L11</u>	L10 and interlayer and electroless	0	<u>L11</u>
<u>L10</u>	cobalt near3 (capping adj layer)	44	<u>L10</u>
<u>L9</u>	L7 and interlayer and dielectric and copper	0	<u>L9</u>
<u>L8</u>	L7 and electroless	1	<u>L8</u>
<u>L7</u>	ultra adj sonic adj energy	84	<u>L7</u>
<u>L6</u>	L1 and (sonic adj energy)	0	<u>L6</u>
<u>L5</u>	L1 and capping	0	<u>L5</u>
<u>L4</u>	L1 and (cobalt near2 capping)	0	<u>L4</u>
<u>L3</u>	L1 and copper	4	<u>L3</u>
<u>L2</u>	L1 and (plurality near5 copper)	0	<u>L2</u>
<u>L1</u>	hydrophobic near2 interlayer	22	<u>L1</u>

END OF SEARCH HISTORY

Hit List

Search Results - Record(s) 1 through 2 of 2 returned.

1. Document ID: US 6853049 B2

L13: Entry 1 of 2

File: USPT

Feb 8, 2005

US-PAT-NO: 6853049

DOCUMENT-IDENTIFIER: US 6853049 B2

TITLE: Silicide-silicon oxide-semiconductor antifuse device and method of making

2. Document ID: US 6268985 B1

L13: Entry 2 of 2

File: USPT

Jul 31, 2001

US-PAT-NO: 6268985

DOCUMENT-IDENTIFIER: US 6268985 B1

TITLE: Read head having spin valve sensor with improved capping layer

Terms	Documents
L12 and copper	2

Display Format:

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Search Results - Record(s) 1 through 4 of 4 returned.

1. Document ID: US 6815207 B2

L3: Entry 1 of 4

File: USPT

Nov 9, 2004

US-PAT-NO: 6815207

DOCUMENT-IDENTIFIER: US 6815207 B2

TITLE: Moisture/wetness detecting method, moisture/wetness detecting label, articles with moisture/wetness detecting function, and detecting material and method

[Full](#) [Title](#) [Citation](#) [Front](#) [Review](#) [Classification](#) [Date](#) [Reference](#) [Claims](#) [KMC](#) [Drawn](#)

2. Document ID: US 5866287 A

L3: Entry 2 of 4

File: USPT

Feb 2, 1999

US-PAT-NO: 5866287

DOCUMENT-IDENTIFIER: US 5866287 A

TITLE: Imaging element comprising and electrically-conductive layer containing metal antimonate and non-conductive metal-containing colloidal particles

[Full](#) [Title](#) [Citation](#) [Front](#) [Review](#) [Classification](#) [Date](#) [Reference](#) [Claims](#) [KMC](#) [Drawn](#)

3. Document ID: US 3880657 A

L3: Entry 3 of 4

File: USPT

Apr 29, 1975

US-PAT-NO: 3880657

DOCUMENT-IDENTIFIER: US 3880657 A

** See image for Certificate of Correction **

TITLE: Conducting layer for organic photoconductive element

[Full](#) [Title](#) [Citation](#) [Front](#) [Review](#) [Classification](#) [Date](#) [Reference](#) [Claims](#) [KMC](#) [Drawn](#)

4. Document ID: US 3559576 A

L3: Entry 4 of 4

File: USPT

Feb 2, 1971

US-PAT-NO: 3559576

DOCUMENT-IDENTIFIER: US 3559576 A

TITLE: PLANOGRAPHIC REVERSED PRINTING

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [References](#) | [Claims](#) | [TOC](#) | [Print](#)[Clear](#)[Generate Collection](#)[Print](#)[Fwd Refs](#)[Bkwd Refs](#)[Generate OACS](#)

Terms

Documents

L1 and copper

4

Display Format: [Change Format](#)[Previous Page](#)[Next Page](#)[Go to Doc#](#)

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Search Results - Record(s) 1 through 1 of 1 returned.

1. Document ID: US 6846725 B2

L8: Entry 1 of 1

File: USPT

Jan 25, 2005

US-PAT-NO: 6846725

DOCUMENT-IDENTIFIER: US 6846725 B2

TITLE: Wafer-level package for micro-electro-mechanical systems

Terms	Documents
L7 and electroless	1

Display Format:

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Refine Search

Search Results -

Terms	Documents
L14 and cobalt	0

Database: US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
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Search: L17

Search History

DATE: Thursday, March 03, 2005 [Printable Copy](#) [Create Case](#)

Set Name Query
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Hit Count Set Name
 result set

DB=USPT; PLUR=YES; OP=ADJ

<u>L17</u>	L14 and cobalt	0	<u>L17</u>
<u>L16</u>	L14 and (cu or copper) and cobalt	0	<u>L16</u>
<u>L15</u>	L14 and copper	3	<u>L15</u>
<u>L14</u>	L7 and dielectric	8	<u>L14</u>
<u>L13</u>	L12 and copper	2	<u>L13</u>
<u>L12</u>	L10 and interlayer	8	<u>L12</u>
<u>L11</u>	L10 and interlayer and electroless	0	<u>L11</u>
<u>L10</u>	cobalt near3 (capping adj layer)	44	<u>L10</u>
<u>L9</u>	L7 and interlayer and dielectric and copper	0	<u>L9</u>
<u>L8</u>	L7 and electroless	1	<u>L8</u>
<u>L7</u>	ultra adj sonic adj energy	84	<u>L7</u>
<u>L6</u>	L1 and (sonic adj energy)	0	<u>L6</u>
<u>L5</u>	L1 and capping	0	<u>L5</u>
<u>L4</u>	L1 and (cobalt near2 capping)	0	<u>L4</u>

<u>L3</u>	L1 and copper	4	<u>L3</u>
<u>L2</u>	L1 and (plurality near5 copper)	0	<u>L2</u>
<u>L1</u>	hydrophobic near2 interlayer	22	<u>L1</u>

END OF SEARCH HISTORY

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Search Results - Record(s) 1 through 3 of 3 returned.

1. Document ID: US 6846725 B2

L15: Entry 1 of 3

File: USPT

Jan 25, 2005

US-PAT-NO: 6846725

DOCUMENT-IDENTIFIER: US 6846725 B2

TITLE: Wafer-level package for micro-electro-mechanical systems

[Full](#) [Title](#) [Citation](#) [Front](#) [Review](#) [Classification](#) [Date](#) [Reference](#) [Claims](#) [KWD](#) [Drawings](#)

2. Document ID: US 4360706 A

L15: Entry 2 of 3

File: USPT

Nov 23, 1982

US-PAT-NO: 4360706

DOCUMENT-IDENTIFIER: US 4360706 A

TITLE: Electric cables of reduced micro-voids in the extruded insulation

[Full](#) [Title](#) [Citation](#) [Front](#) [Review](#) [Classification](#) [Date](#) [Reference](#) [Claims](#) [KWD](#) [Drawings](#)

3. Document ID: US 4259281 A

L15: Entry 3 of 3

File: USPT

Mar 31, 1981

US-PAT-NO: 4259281

DOCUMENT-IDENTIFIER: US 4259281 A

** See image for Certificate of Correction **

TITLE: Process for reducing micro-voids in the extruded insulation of electric cables

[Full](#) [Title](#) [Citation](#) [Front](#) [Review](#) [Classification](#) [Date](#) [Reference](#) [Claims](#) [KWD](#) [Drawings](#)

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Terms	Documents
L14 and copper	3

Display Format: [Change Format](#)

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Refine Search

Search Results -

Terms	Documents
L22 and cobalt	0

Database: US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search: L23

Search History

DATE: Thursday, March 03, 2005 [Printable Copy](#) [Create Case](#)

Set Name Query
 side by side

Hit Count Set Name
 result set

DB=USPT; PLUR=YES; OP=ADJ

<u>L23</u>	L22 and cobalt	0	<u>L23</u>
<u>L22</u>	L19 and electroless	5	<u>L22</u>
<u>L21</u>	L19 and (electroless near bath)	0	<u>L21</u>
<u>L20</u>	L19 and (ultra adj sonic adj energy)	0	<u>L20</u>
<u>L19</u>	L18 and (capping adj layer)	23	<u>L19</u>
<u>L18</u>	copper near7 interlayer	677	<u>L18</u>
<u>L17</u>	L14 and cobalt	0	<u>L17</u>
<u>L16</u>	L14 and (cu or copper) and cobalt	0	<u>L16</u>
<u>L15</u>	L14 and copper	3	<u>L15</u>
<u>L14</u>	L7 and dielectric	8	<u>L14</u>
<u>L13</u>	L12 and copper	2	<u>L13</u>
<u>L12</u>	L10 and interlayer	8	<u>L12</u>
<u>L11</u>	L10 and interlayer and electroless	0	<u>L11</u>
<u>L10</u>	cobalt near3 (capping adj layer)	44	<u>L10</u>

<u>L9</u>	L7 and interlayer and dielectric and copper	0	<u>L9</u>
<u>L8</u>	L7 and electroless	1	<u>L8</u>
<u>L7</u>	ultra adj sonic adj energy	84	<u>L7</u>
<u>L6</u>	L1 and (sonic adj energy)	0	<u>L6</u>
<u>L5</u>	L1 and capping	0	<u>L5</u>
<u>L4</u>	L1 and (cobalt near2 capping)	0	<u>L4</u>
<u>L3</u>	L1 and copper	4	<u>L3</u>
<u>L2</u>	L1 and (plurality near5 copper)	0	<u>L2</u>
<u>L1</u>	hydrophobic near2 interlayer	22	<u>L1</u>

END OF SEARCH HISTORY

Hit List

Search Results - Record(s) 1 through 5 of 5 returned.

1. Document ID: US 6800554 B2

L22: Entry 1 of 5

File: USPT

Oct 5, 2004

US-PAT-NO: 6800554

DOCUMENT-IDENTIFIER: US 6800554 B2

TITLE: Copper alloys for interconnections having improved electromigration characteristics and methods of making same

2. Document ID: US 6562416 B2

L22: Entry 2 of 5

File: USPT

May 13, 2003

US-PAT-NO: 6562416

DOCUMENT-IDENTIFIER: US 6562416 B2

TITLE: Method of forming low resistance vias

3. Document ID: US 6486055 B1

L22: Entry 3 of 5

File: USPT

Nov 26, 2002

US-PAT-NO: 6486055

DOCUMENT-IDENTIFIER: US 6486055 B1

TITLE: Method for forming copper interconnections in semiconductor component using electroless plating system

4. Document ID: US 6462417 B1

L22: Entry 4 of 5

File: USPT

Oct 8, 2002

US-PAT-NO: 6462417

DOCUMENT-IDENTIFIER: US 6462417 B1

TITLE: Coherent alloy diffusion barrier for integrated circuit interconnects

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KWC](#) | [Draws](#)

5. Document ID: US 6445070 B1

L22: Entry 5 of 5

File: USPT

Sep 3, 2002

US-PAT-NO: 6445070

DOCUMENT-IDENTIFIER: US 6445070 B1

TITLE: Coherent carbide diffusion barrier for integrated circuit interconnects

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KWC](#) | [Draws](#)

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Terms

Documents

L19 and electroless

5

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Refine Search

Search Results -

Terms	Documents
L30 and cobalt	4

Database: US Pre-Grant Publication Full-Text Database
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 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L31

Refine Search

Recall Text

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Interrupt

Search History

DATE: Thursday, March 03, 2005 [Printable Copy](#) [Create Case](#)

Set Name Query
 side by side

Hit Count Set Name
 result set

DB=USPT; PLUR=YES; OP=ADJ

<u>L31</u>	L30 and cobalt	4	<u>L31</u>
<u>L30</u>	L25 and electroless	4	<u>L30</u>
<u>L29</u>	L25 and power	5	<u>L29</u>
<u>L28</u>	L25 and watts	0	<u>L28</u>
<u>L27</u>	L25 and hertz	0	<u>L27</u>
<u>L26</u>	L25 and (sonic adj energy)	0	<u>L26</u>
<u>L25</u>	L24 and interlayer	11	<u>L25</u>
<u>L24</u>	copper near9 hydrophobic	205	<u>L24</u>
<u>L23</u>	L22 and cobalt	0	<u>L23</u>
<u>L22</u>	L19 and electroless	5	<u>L22</u>
<u>L21</u>	L19 and (electroless near bath)	0	<u>L21</u>
<u>L20</u>	L19 and (ultra adj sonic adj energy)	0	<u>L20</u>
<u>L19</u>	L18 and (capping adj layer)	23	<u>L19</u>
<u>L18</u>	copper near7 interlayer	677	<u>L18</u>

<u>L17</u>	L14 and cobalt	0	<u>L17</u>
<u>L16</u>	L14 and (cu or copper) and cobalt	0	<u>L16</u>
<u>L15</u>	L14 and copper	3	<u>L15</u>
<u>L14</u>	L7 and dielectric	8	<u>L14</u>
<u>L13</u>	L12 and copper	2	<u>L13</u>
<u>L12</u>	L10 and interlayer	8	<u>L12</u>
<u>L11</u>	L10 and interlayer and electroless	0	<u>L11</u>
<u>L10</u>	cobalt near3 (capping adj layer)	44	<u>L10</u>
<u>L9</u>	L7 and interlayer and dielectric and copper	0	<u>L9</u>
<u>L8</u>	L7 and electroless	1	<u>L8</u>
<u>L7</u>	ultra adj sonic adj energy	84	<u>L7</u>
<u>L6</u>	L1 and (sonic adj energy)	0	<u>L6</u>
<u>L5</u>	L1 and capping	0	<u>L5</u>
<u>L4</u>	L1 and (cobalt near2 capping)	0	<u>L4</u>
<u>L3</u>	L1 and copper	4	<u>L3</u>
<u>L2</u>	L1 and (plurality near5 copper)	0	<u>L2</u>
<u>L1</u>	hydrophobic near2 interlayer	22	<u>L1</u>

END OF SEARCH HISTORY

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Search Results - Record(s) 1 through 4 of 4 returned.

1. Document ID: US 6838772 B2

L31: Entry 1 of 4

File: USPT

Jan 4, 2005

US-PAT-NO: 6838772

DOCUMENT-IDENTIFIER: US 6838772 B2

TITLE: Semiconductor device

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KM/C	Drawn Ds
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2. Document ID: US 6730594 B2

L31: Entry 2 of 4

File: USPT

May 4, 2004

US-PAT-NO: 6730594

DOCUMENT-IDENTIFIER: US 6730594 B2

TITLE: Method for manufacturing semiconductor device

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KM/C	Drawn Ds
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3. Document ID: US 6723631 B2

L31: Entry 3 of 4

File: USPT

Apr 20, 2004

US-PAT-NO: 6723631

DOCUMENT-IDENTIFIER: US 6723631 B2

TITLE: Fabrication method of semiconductor integrated circuit device

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KM/C	Drawn Ds
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4. Document ID: US 3944440 A

L31: Entry 4 of 4

File: USPT

Mar 16, 1976

US-PAT-NO: 3944440

DOCUMENT-IDENTIFIER: US 3944440 A

TITLE: Selective reflecting metal/metal oxide coatings using surfactant to promote

uniform oxidation

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Search](#) | [Claims](#) | [TOC](#) | [Drawings](#)

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Terms	Documents
L30 and cobalt	4

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Day : Thursday

PALM INTRANET

18/84,592

Date: 3/3/2005
Time: 21:22:15**Inventor Name Search Result**

Your Search was:

Last Name = BRASK

First Name = JUSTIN

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>10808021</u>	Not Issued	030	03/23/2004	STRAINED SILICON WITH REDUCED ROUGHNESS	BRASK, JUSTIN
<u>10949994</u>	Not Issued	020	09/23/2004	U-GATE TRANSISTORS AND METHODS OF FABRICATION	BRASK, JUSTIN
<u>10977261</u>	Not Issued	030	10/29/2004	RESONANT TUNNELING DEVICE USING METAL OXIDE SEMICONDUCTOR PROCESSING	BRASK, JUSTIN
<u>10209843</u>	6861005	150	07/31/2002	GENERATING NITRIDE WAVEGUIDES	BRASK, JUSTIN K.
<u>10210461</u>	6797622	150	07/31/2002	SELECTIVE ETCHING OF POLYSILICON	BRASK, JUSTIN K.
<u>10242740</u>	6770568	150	09/12/2002	SELECTIVE ETCHING USING SONICATION	BRASK, JUSTIN K.
<u>10260591</u>	6746967	150	09/30/2002	ETCHING METAL USING SONICATION	BRASK, JUSTIN K.
<u>10271446</u>	Not Issued	083	10/15/2002	PROTECTING DELICATE SEMICONDUCTOR FEATURES DURING WET ETCHING	BRASK, JUSTIN K.
<u>10272624</u>	Not Issued	083	10/17/2002	WET ETCHING NARROW TRENCHES	BRASK, JUSTIN K.
<u>10273474</u>	6743740	150	10/18/2002	USING SONIC ENERGY IN CONNECTION WITH LASER-ASSISTED DIRECT IMPRINTING	BRASK, JUSTIN K.
<u>10278535</u>	Not Issued	041	10/23/2002	REMOVING FLUORINE-BASED PLASMA ETCH RESIDUES	BRASK, JUSTIN K.
<u>10294266</u>	Not Issued	061	11/14/2002	CONTROLLED USE OF PHOTOCHEMICALLY SUSCEPTIBLE CHEMISTRIES FOR ETCHING, CLEANING AND SURFACE CONDITIONING	BRASK, JUSTIN K.

<u>10295150</u>	6624127	150	11/15/2002	HIGHLY POLAR CLEANS FOR REMOVAL OF RESIDUES FROM SEMICONDUCTOR STRUCTURES	BRASK, JUSTIN K.
<u>10301038</u>	Not Issued	041	11/20/2002	OXIDATION INHIBITOR FOR WET ETCHING PROCESSES	BRASK, JUSTIN K.
<u>10305684</u>	Not Issued	083	11/26/2002	SACRIFICIAL ANNEALING LAYER FOR A SEMICONDUCTOR DEVICE AND A METHOD OF FABRICATION	BRASK, JUSTIN K.
<u>10327293</u>	6858483	150	12/20/2002	INTEGRATING N-TYPE AND P-TYPE METAL GATE TRANSISTORS	BRASK, JUSTIN K.
<u>10338174</u>	6709911	150	01/07/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
<u>10382452</u>	Not Issued	094	03/06/2003	ACOUSTIC STREAMING OF CONDENSATE DURING SPUTTERED METAL VAPOR DEPOSITION	BRASK, JUSTIN K.
<u>10387303</u>	6716707	150	03/11/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
<u>10391816</u>	6696327	150	03/18/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
<u>10395447</u>	6737365	150	03/24/2003	FORMING A POROUS DIELECTRIC LAYER	BRASK, JUSTIN K.
<u>10397924</u>	Not Issued	041	03/25/2003	REMOVING SILICON NANO-CRYSTALS	BRASK, JUSTIN K.
<u>10421557</u>	Not Issued	041	04/21/2003	METHOD AND APPARATUS FOR PARTICLE REMOVAL	BRASK, JUSTIN K.
<u>10441616</u>	6806146	150	05/20/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
<u>10454109</u>	Not Issued	030	06/04/2003	HIGHLY POLAR CLEANS FOR REMOVAL OF RESIDUES FROM SEMICONDUCTOR STRUCTURES	BRASK, JUSTIN K.
<u>10464016</u>	Not Issued	061	06/17/2003	CHEMICAL THINNING OF SILICON BODY OF AN SOI	BRASK, JUSTIN K.

				SUBSTRATE	
<u>10607955</u>	Not Issued	030	06/26/2003	SELECTIVE SURFACE EXPOSURE, CLEANS, AND CONDITIONING OF THE GERMANIUM FILM IN A GE PHOTODETECTOR	BRASK, JUSTIN K.
<u>10608669</u>	Not Issued	030	06/27/2003	USING BIDENTATE CHELATORS TO CLEAN SEMICONDUCTOR WAFERS	BRASK, JUSTIN K.
<u>10622955</u>	Not Issued	041	07/18/2003	ETCHING METAL SILICIDES AND GERMANIDES	BRASK, JUSTIN K.
<u>10626336</u>	Not Issued	061	07/24/2003	FORMING A HIGH DIELECTRIC CONSTANT FILM USING METALLIC PRECURSOR	BRASK, JUSTIN K.
<u>10629127</u>	Not Issued	040	07/29/2003	PREVENTING SILICIDE FORMATION AT THE GATE ELECTRODE IN A REPLACEMENT METAL GATE TECHNOLOGY	BRASK, JUSTIN K.
<u>10632470</u>	6855639	150	08/01/2003	PRECISE PATTERNING OF HIGH-K FILMS	BRASK, JUSTIN K.
<u>10652546</u>	Not Issued	030	08/28/2003	SELECTIVE ETCH PROCESS FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
<u>10652796</u>	Not Issued	071	08/28/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
<u>10658225</u>	Not Issued	030	09/08/2003	METHODS AND COMPOSITIONS FOR SELECTIVELY ETCHING METAL FILMS AND STRUCTURES	BRASK, JUSTIN K.
<u>10692696</u>	Not Issued	071	10/24/2003	EPITAXIALLY DEPOSITED SOURCE/DRAIN	BRASK, JUSTIN K.
<u>10696204</u>	Not Issued	071	10/29/2003	DEPOSITING AN OXIDE	BRASK, JUSTIN K.
<u>10704497</u>	Not Issued	089	11/06/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A METAL GATE ELECTRODE	BRASK, JUSTIN K.
<u>10704498</u>	Not Issued	030	11/06/2003	METHOD FOR ETCHING A THIN METAL LAYER	BRASK, JUSTIN K.

<u>10716321</u>	Not Issued	092	11/17/2003	SACRIFICIAL ANNEALING LAYER FOR A SEMICONDUCTOR DEVICE AND A METHOD OF FABRICATION	BRASK, JUSTIN K.
<u>10721448</u>	Not Issued	030	11/24/2003	METHOD OF SMOOTHING WAVEGUIDE STRUCTURES	BRASK, JUSTIN K.
<u>10739173</u>	Not Issued	030	12/18/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE THAT INCLUDES A METAL GATE ELECTRODE	BRASK, JUSTIN K.
<u>10742678</u>	Not Issued	019	12/19/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE WITH A METAL GATE ELECTRODE THAT IS FORMED ON AN ANNEALED HIGH-K GATE DIELECTRIC LAYER	BRASK, JUSTIN K.
<u>10746323</u>	Not Issued	041	12/23/2003	METHOD OF FABRICATING SEMICONDUCTOR DEVICES WITH REPLACEMENT, COAXIAL GATE STRUCTURE	BRASK, JUSTIN K.
<u>10748090</u>	Not Issued	092	12/29/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
<u>10748345</u>	Not Issued	030	12/29/2003	METHODS FOR FABRICATING METAL GATE STRUCTURES	BRASK, JUSTIN K.
<u>10748383</u>	Not Issued	030	12/29/2003	METHODS FOR INTEGRATING REPLACEMENT METAL GATE STRUCTURES	BRASK, JUSTIN K.
<u>10748545</u>	Not Issued	030	12/29/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE THAT INCLUDES A METAL GATE ELECTRODE	BRASK, JUSTIN K.
<u>10748559</u>	Not Issued	041	12/29/2003	CMOS DEVICE WITH METAL AND SILICIDE GATE ELECTRODES AND A METHOD FOR MAKING IT	BRASK, JUSTIN K.
<u>10749196</u>	Not Issued	030	12/30/2003	REPLACEMENT GATE FLOW FACILITATING HIGH YIELD AND INCORPORATION OF ETCH STOP LAYERS AND/OR STRESSED FILMS	BRASK, JUSTIN K.

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